



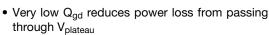
N-Channel 100 V (D-S) MOSFET



PRODUCT SUMMARY					
V _{DS} (V)	100				
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 10 \text{ V}$	0.0035				
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 7.5 \text{ V}$	0.0037				
Q _g typ. (nC)	142.4				
I _D (A) ^d	150				
Configuration	Single				

FEATURES

- TrenchFET® power MOSFET
- Maximum 175 °C junction temperature

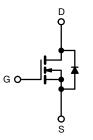




- 100 % R_a and UIS tested
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

APPLICATIONS

- Power supply
 - Secondary synchronous rectification
- DC/DC converter
- Power tools
- · Motor drive switch
- DC/AC inverter
- · Battery management
- OR-ing / e-fuse



N-Channel MOSFET

ORDERING INFORMATION			
Package	D ² PAK (TO-263-7L)		
Lead (Pb)-free and halogen-free	SUM70030M-GE3		

PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-source voltage		V _{DS}	100	
Gate-source voltage		V _{GS}	± 20	V
O a library and a library and (T. 150.00)	T _C = 25 °C		150 ^d	
Continuous drain current (T _J = 150 °C)	T _C = 70 °C	l _D	150 ^d	
Pulsed drain current (t = 100 μs)		I _{DM}	500	A
Avalanche current		I _{AS}	60	
Single avalanche energy ^a	L = 0.1 mH	E _{AS}	180	mJ
Maximum newer discipation 8	T _C = 25 °C	В	375 ^b	W
Maximum power dissipation ^a	T _C = 125 °C	P _D	125 ^b	
Operating junction and storage temperature range		T _J , T _{stq}	-55 to +175	°C

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	LIMIT	UNIT	
Junction-to-ambient (PCB mount) ^c	R_{thJA}	40	°C/W	
Junction-to-case (drain)	R_{thJC}	0.4	C/VV	

Notes

- a. Duty cycle ≤ 1 %
- b. See SOA curve for voltage derating

S20-0694-Rev. A, 14-Sep-2020

- c. When mounted on 1" square PCB (FR4 material)
- d. Package limited



Vishay Siliconix

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-source breakdown voltage	V_{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	100	-	-	V
Gate threshold voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu A$	2	-	4	
Gate-body leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	-	-	± 250	nA
		V _{DS} = 100 V, V _{GS} = 0 V	-	-	1	μА
Zero gate voltage drain current	I _{DSS}	V _{DS} = 100 V, V _{GS} = 0 V, T _J = 125 °C	-	-	150	
		V _{DS} = 100 V, V _{GS} = 0 V, T _J = 175 °C	-	-	5	mA
On-state drain current ^a	I _{D(on)}	V _{DS} ≥ 10 V, V _{GS} = 10 V	120	-	-	Α
Duning and an alternative and 3	Б	$V_{GS} = 10 \text{ V}, I_D = 30 \text{ A}$	-	0.0029	0.0035	Ω
Drain-source on-state resistance ^a	R _{DS(on)}	$V_{GS} = 7.5 \text{ V}, I_D = 20 \text{ A}$	-	0.0031	0.0037	
Forward transconductance a	9 _{fs}	$V_{DS} = 15 \text{ V}, I_D = 30 \text{ A}$	-	110	-	S
Dynamic ^b						
Input capacitance	C _{iss}		-	10 870	-	
Output capacitance	C _{oss}	$V_{GS} = 0 \text{ V}, V_{DS} = 50 \text{ V}, f = 1 \text{ MHz}$	-	820	-	pF
Reverse transfer capacitance	C _{rss}		-	40	-	
Total gate charge ^c	Qg		-	142.4	214	
Gate-source charge ^c	Q _{gs}	$V_{DS} = 50 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 20 \text{ A}$	-	46.8	-	nC
Gate-drain charge ^c	Q _{gd}		-	18.5	-	
Output charge	Q _{oss}	V _{DS} = 50 V, V _{GS} = 0 V	-	138	207	
Gate resistance	R_g	f = 1 MHz	0.34	1.7	3.4	Ω
Turn-on delay time ^c	t _{d(on)}		-	30	60	
Rise time ^c	t _r	$V_{DD} = 50 \text{ V}, R_{L} = 3 \Omega$	-	13	26	
Turn-off delay time ^c	t _{d(off)}	$I_D \cong 10 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$	-	50	100	ns
Fall time ^c	t _f		-	15	30	
Drain-Source Body Diode Ratings a	and Characte	ristics ^b (T _C = 25 °C)				
Pulsed current (t = 100 μs)	I _{SM}		-	-	250	Α
Forward voltage ^a	V _{SD}	I _F = 10 A, V _{GS} = 0 V	-	0.8	1.5	V
Reverse recovery time	t _{rr}		-	76	150	ns
Peak reverse recovery charge	I _{RM(REC)}	I _F = 34 A, di/dt = 100 A/μs	-	4.6	5.6	Α
Reverse recovery charge	Q _{rr}		-	0.205	0.24	μC
Reverse recovery fall time	ta	·	-	52	-	
Reverse recovery rise time	t _b		-	24	-	ns

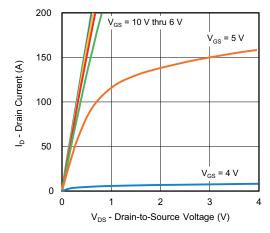
Notes

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

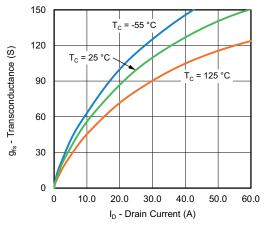
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



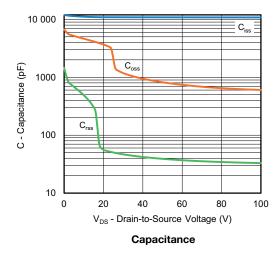
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

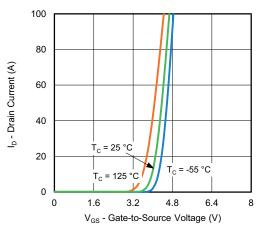


Output Characteristics

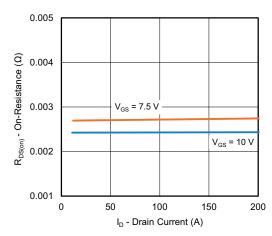


Transconductance

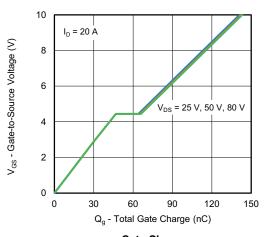




Transfer Characteristics



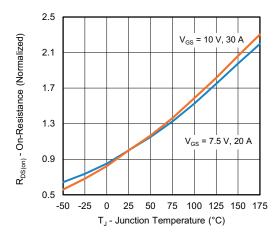
On-Resistance vs. Drain Current



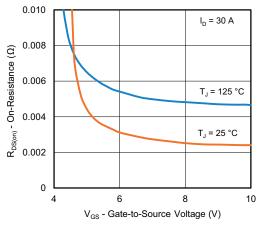
Gate Charge



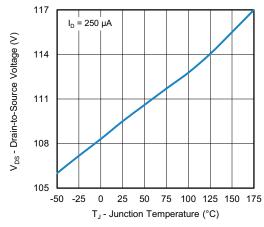
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



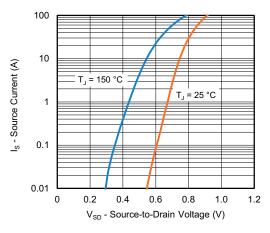
On-Resistance vs. Junction Temperature



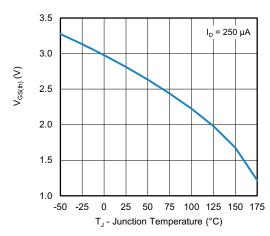
On-Resistance vs. Gate-to-Source Voltage



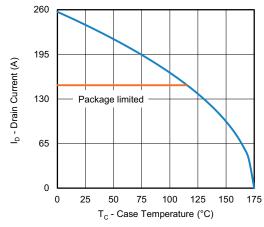
Drain Source Breakdown vs. Junction Temperature



Source Drain Diode Forward Voltage



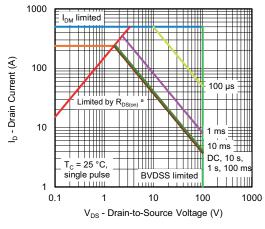
Threshold Voltage



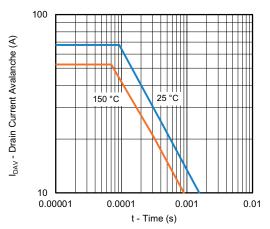
Current Derating



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



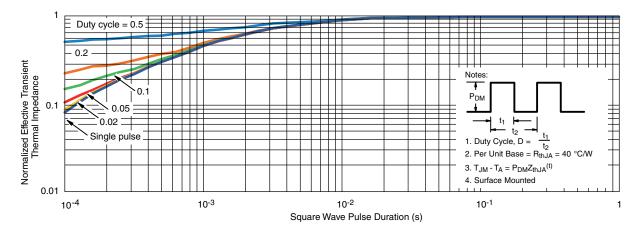
Safe Operating Area



Single Pulse Avalanche Current Capability vs. Time

Note

a. $V_{GS} > minimum V_{GS}$ at which $R_{DS(on)}$



Normalized Thermal Transient Impedance, Junction-to-Case

Note

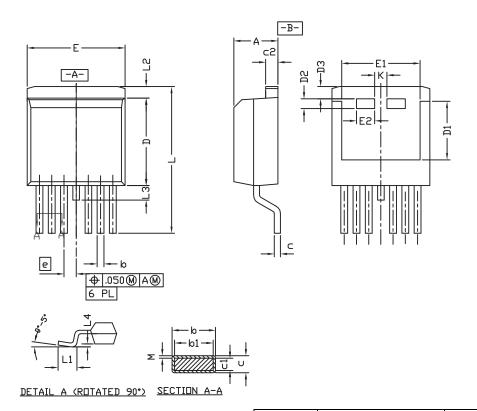
- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction to Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction to Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

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D²PAK (TO-263-7L) Case Outline



Notes

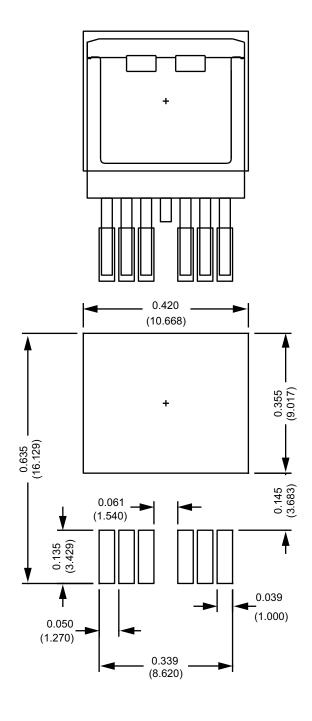
- 1. Plane B includes maximum features of heat sink tab and plastic
- 2. No more than 25 % of L1 can fall above seating plane by max. 8 mils
- 3. Pin to pin coplanarity max. 4 mils
- 4. Lead thickness 25 mils
- 5. For SUM part numbers lead thickness is 24 mils to 29 mils
- 6. For reference only
- 7. Use inches as the primary measurement
- 8. This feature is only for SUM

	INCHES		MILLIMETERS		
DIM.	MIN.	MAX.	MIN.	MAX.	
Α	0.160	0.190	4.064	4.826	
b	0.020	0.039	0.508	0.990	
b1	0.020	0.035	0.508	0.889	
c* SUB	0.012	0.018	0.305	0.457	
c* SUM	0.022	0.028	0.559	0.711	
c1	0.018	0.025	0.457	0.635	
c2	0.045	0.055	1.143	1.397	
D	0.340	0.380	8.636	9.652	
D1	0.260	0.280	6.604	7.112	
D2	0.046	0.050	1.168	1.270	
D3	0.045	0.055	1.143	1.397	
Е	0.380	0.410	9.652	10.414	
E1	0.245	-	6.223	-	
E2	0.072	0.078	1.829	1.981	
е	0.050 BSC		1.27 BSC		
K	0.045	0.055	1.143	1.397	
L	0.575	0.625	14.605	15.875	
L1	0.090	0.110	2.286	2.794	
L2	0.040	0.055	1.016	1.397	
L3	0.050	0.070	1.270	1.778	
L4	0.010 BSC		0.254 BSC		
М	-	0.002	-	0.050	
ECN: T22-0410-Rev. D, 19-Sep-2022 DWG: 6006					

Revision: 19-Sep-2022 Document Number: 63782



Recommended Land Pattern D²PAK (TO-263-7L)





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